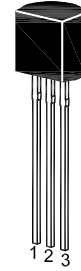


NPN Silicon Epitaxial Planar Transistor

VHF / UHF Transistor.


 1. Emitter 2. Base 3. Collector
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

| Parameter | Symbol | Value | Unit |
|---------------------------|-----------|---------------|------------------|
| Collector Base Voltage | V_{CBO} | 30 | V |
| Collector Emitter Voltage | V_{CEO} | 25 | V |
| Emitter Base Voltage | V_{EBO} | 3 | V |
| Collector Current | I_C | 100 | mA |
| Power Dissipation | P_{tot} | 350 | mW |
| Junction Temperature | T_j | 150 | $^\circ\text{C}$ |
| Storage Temperature Range | T_{stg} | - 55 to + 150 | $^\circ\text{C}$ |

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

| Parameter | Symbol | Min. | Max. | Unit |
|--|---------------|-------------|-------------|----------|
| DC Current Gain at $V_{CE} = 10\text{ V}$, $I_C = 4\text{ mA}$ | h_{FE} | 60 | - | - |
| Collector Base Cutoff Current at $V_{CB} = 25\text{ V}$ | I_{CBO} | - | 100 | nA |
| Emitter Base Cutoff Current at $V_{EB} = 2\text{ V}$ | I_{EBO} | - | 100 | nA |
| Collector Base Breakdown Voltage at $I_C = 100\text{ }\mu\text{A}$ | $V_{(BR)CBO}$ | 30 | - | V |
| Collector Emitter Breakdown Voltage at $I_C = 1\text{ mA}$ | $V_{(BR)CEO}$ | 25 | - | V |
| Emitter Base Breakdown Voltage at $I_E = 10\text{ }\mu\text{A}$ | $V_{(BR)EBO}$ | 3 | - | V |
| Collector Emitter Saturation Voltage at $I_C = 4\text{ mA}$, $I_B = 0.4\text{ mA}$ | $V_{CE(sat)}$ | - | 0.5 | V |
| Base Emitter On Voltage at $V_{CE} = 10\text{ V}$, $I_C = 4\text{ mA}$ | $V_{BE(on)}$ | - | 0.95 | V |
| Current Gain Bandwidth Product at $V_{CE} = 10\text{ V}$, $I_C = 4\text{ mA}$, $f = 100\text{ MHz}$ | f_T | 650 | - | MHz |
| Collector Base Capacitance at $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$ | C_{cb} | - | 0.7 | pF |
| Collector Base Feedback Capacitance at $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$ | C_{rb} | 0.35 0.6 | 0.65 0.9 | pF pF |

 MPSA10
MPSA11

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